

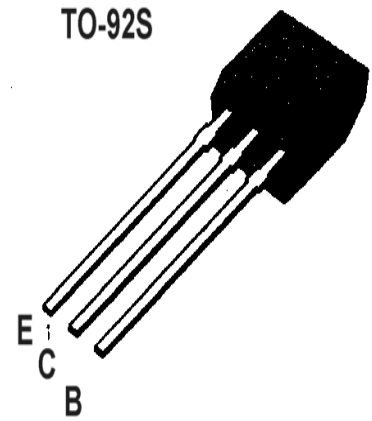
PNP Transistors

—PNP Silicon—

■■ APPLICATION: General purpose applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-40	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-0.2	A
Collector Power Dissipation	P _C	0.3	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C, RG=10Ω)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION	
Collector-Base Breakdown Voltage	BV _{CBO}	-40			V	I _C =-0.1mA	I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40			V	I _C =-1mA	I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E =-0.1mA	I _C =0
Collector Cut-off Current	I _{CEX}			-0.05	uA	V _{CE} =-30V	V _{BE} =-3V
Emitter Cut-off Current	I _{BEX}			-0.05	uA	V _{CE} =-30V	V _{BE} =-3V
Base-Emitter Saturation Voltage	V _{BE(sat)}			-0.95	V	I _C =-50mA	I _B =-5mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.4	V	I _C =-50mA	I _B =-5mA
DC Current Gain	H _{FE}	80		300	β	V _{CE} =-1V	I _C =-10mA
Gain bandwidth product	f _T	250			MHz	V _{CE} =-20V	I _E =-10mA f=100MHz
Common Base Output Capacitance	Cob			4.5	pF	V _{CB} =-10V	I _E =0 f=1MHz
Turn on Time	t _{on}			70	ns	V _{cc} =-3V	I _c =-10mA I _{B1} =-1mA
Turn off Time	t _{off}			300	ns	V _{cc} =-3V	I _{B1,2} =-1mA I _c =-10mA

■■ H_{FE} Classification And Marking

Print Mark	3906S
Classification	
H _{FE}	80~300